









SN54HC640, SN74HC640

JAJSP51E – JANUARY 1996 – REVISED SEPTEMBER 2022

# SNx4HC6403ステート出力、オクタル・バス・トランシーバ

## 1 特長

- 幅広い動作電圧範囲:2V~6V
- 大電流 3 ステート出力により最大 10 個の LSTTL 負 荷を駆動可能
- 低消費電力、最大 Icc 80µA
- t<sub>pd</sub> = 8ns (標準値)
- 5Vで ±4mA の出力駆動能力
- 低い入力電流:最大 1µA
- 反転ロジック

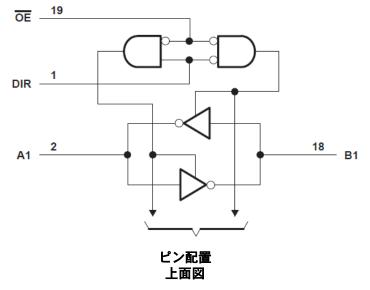
## 2 概要

SNx4HC640 は、3 ステート出力を備えたオクタル・バス・ トランシーバです。8 つのチャネルはすべて、方向 (DIR) ピンと出力イネーブル (OE) ピンにより制御されます。

## 製品情報(1)

部品番号	パッケージ	本体サイズ (公称)							
SN54HC640	J (CDIP, 20)	26.92mm × 6.92mm							
	DW (SOIC, 20)	12.80mm × 7.50mm							
SN74HC640	N (PDIP, 20)	25.40mm × 6.35mm							
311/4110040	NS (SO, 20)	15.00mm × 5.30mm							
	PW (TSSOP, 20)	4.40mm × 6.50mm							

(1) 利用可能なパッケージについては、このデータシートの末尾にあ る注文情報を参照してください。





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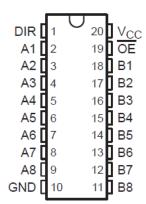
# **3 Revision History**

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

CI	nanges from Revision D (August 2003) to Rev	n E (September 2022) Pag	је
•	最新のデータシート規格を反映するように、文書全	採番、書式設定、表、図、相互参照を更新	.1



# **4 Pin Configuration and Functions**



J, DW, N, NS, or PW Package 20-Pin CDIP, SOIC, PDIP, SO, TSSOP Top View

## **5 Specifications**

## 5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage range		-0.5	7	V
I <sub>IK</sub>	Input clamp current <sup>(2)</sup>	(V <sub>I</sub> < 0 or V <sub>I</sub> > V <sub>CC</sub> )		±20	mA
I <sub>OK</sub>	Output clamp current <sup>(2)</sup>	(V <sub>O</sub> < 0 or V <sub>O</sub> > V <sub>CC</sub> )		±20	mA
Io	Continuous output current	(V <sub>O</sub> = 0 to V <sub>CC</sub> )		±35	mA
V <sub>CC</sub> or GND	Continuous current through			±70	mA
T <sub>J</sub>	Junction temperature			150	°C
T <sub>stg</sub>	Storage temperature		-65	150	°C

<sup>(1)</sup> Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

## 5.2 Recommended Operating Conditions<sup>(1)</sup>

			SN	154HC640		SN74HC640			LINUT
			MIN	NOM	MAX	MIN	NOM	MAX	UNIT
V <sub>CC</sub>	Supply voltage		2	5	6	2	5	6	V
		V <sub>CC</sub> = 2 V	1.5			1.5			
V <sub>IH</sub>	High-level input voltage	V <sub>CC</sub> = 4.5 V	3.15			3.15			v
		V <sub>CC</sub> = 6 V	4.2			4.2			
		V <sub>CC</sub> = 2 V			0.5			0.5	
V <sub>IL</sub>	Low-level input voltage	V <sub>CC</sub> = 4.5 V			1.35			1.35	V
		V <sub>CC</sub> = 6 V			1.8	1	4.2  0.  1.3  1.  0 V <sub>C</sub> 0 V <sub>C</sub>	1.8	
VI	Input voltage	<u>"</u>	0		V <sub>CC</sub>	0		V <sub>CC</sub>	V
Vo	Output voltage		0		V <sub>CC</sub>	0		V <sub>CC</sub>	V
		V <sub>CC</sub> = 2 V			1000			1000	
Δt/Δν	Input transition rise/fall time	V <sub>CC</sub> = 4.5 V			500			500	ns
		V <sub>CC</sub> = 6 V			400	1		400	
T <sub>A</sub>	Operating free-air temperature	·	- 55		125	- 40		85	°C

<sup>(1)</sup> All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report Implications of Slow or Floating SMOS Inputs, literature number SCBA004.

### 5.3 Thermal Information

		DW (SOIC)	N (PDIP)	NS (SO)	PW (TSSOP)	
THER	RMAL METRIC <sup>(1)</sup>	20 PINS	20 PINS	20 PINS	20 PINS	UNIT
$R_{\theta JA}$	Package thermal impedance	58	69	60	83	°C/W

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the Semiconductor and IC package thermal metrics application report.

<sup>(2)</sup> The input and output voltage ratings may be exceeded if the input and output current ratings are observed.



## **5.4 Electrical Characteristics**

	PARAMETER		TEST	V <sub>CC</sub>	T,	4 = 25°C		SN54H	C640	SN74H	C640	UNIT
	PARAMETER		CONDITIONS <sup>(1)</sup>	(V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNII
				2	1.9	1.998		1.9		1.9		
			I <sub>OH</sub> = -20 μA	4.5	4.4	4.400		4.4		4.4		
V <sub>OH</sub>	High-level output voltage			6	5.9	5.999		5.9		5.9		V
			I <sub>OH</sub> = -6 mA	4.5	3.98	4.3		3.7		3.84		
			I <sub>OH</sub> = -7.8 mA	6	5.48	5.8		5.2		5.34		
				2		0.002	0.1		0.1		0.1	
		I <sub>OL</sub> = 20 μA	4.5		0.001	0.1		0.1		0.1		
V <sub>OL</sub>	Low-level output voltage			6		0.001	0.1		0.1		0.1	V
			I <sub>OL</sub> = 6 mA	4.5		0.17	0.26		0.4		0.33	
			I <sub>OL</sub> = 7.8 mA	6		0.15	0.26		0.4		0.33	
I <sub>I</sub>	Input hold current	DIR or OE	$V_I = V_{CC}$ or 0	6		±0.1	±100		±1000		±1000	nA
I <sub>OZ</sub>	Off-state output current	A or B	$V_I = V_{CC}$ or 0. $I_O = 0$	6		±0.01	±0.5		±10		±5	μA
ΔI <sub>CC</sub>	Supply-current change		One input at 0.5V or 2.4 V, Other inputs at 0 or V <sub>CC</sub>	6			8		160		80	μА
Ci	Input capacitance	DIR or OE		2 to 6		3	10		10		10	pF

<sup>(1)</sup>  $V_I = V_{IH}$  or  $V_{IL}$ , unless otherwise noted.

# 5.5 Switching Characteristics

 $C_1 = 50 \text{ pF. See Figure 6}$ 

	DADAMETED	EDOM (INDUT)	TO		T	_ = 25°C		SN54H	C640	SN75H	C640	
	PARAMETER	FROM (INPUT)	(OUTPUT)	V <sub>CC</sub> (V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	
				2		29	105		160		130	
$t_{pd}$	Propagation delay	A or B	Υ	4.5		10	21		32		26	ns
				6		8	18		27		22	
				2		109	230		340		290	
t <sub>en</sub>	Enable time	ŌĒ	A or B	4.5		27	46		68		58	ns
				6		20	39		58		49	
				2		40	150		225		190	
t <sub>dis</sub>	Disable time	ŌĒ	A or B	4.5		18	30		45		38	ns
				6		16	26		38		32	
				2		20	60		90		75	
t <sub>t</sub>	Transition time	n time	A or B	4.5		8	12		18		15	ns
				6		6	10		15		13	

## **5.5 Switching Characteristics**

C<sub>L</sub> = 150 pF. See Figure 6

	PARAMETER	FROM (INPUT)	то			T <sub>A</sub> = 25°C		SN75HC640	
	FARAMETER	PROW (INFOT)	(OUTPUT)	(V)	MIN TY	MAX	MIN MAX	MIN MAX	
	Propagation delay			2	44	190	290	235	
t <sub>pd</sub>		A or B	B or A	4.5	14	1 38	58	47	ns
				6	1	I 33	49	41	
				2	124	315	470	395	
t <sub>en</sub>	Enable time	ŌĒ	A or B	4.5	3	l 63	94	79	ns
				6	2:	3 54	80	68	
				2	4:	5 210	315	265	
t <sub>t</sub>	Transition time		A or B	4.5	1	7 42	63	53	ns
				6	1;	36	53	45	

# **5.6 Operating Characteristics**

T<sub>A</sub> = 25°C

	Test Conditions	TYP	UNIT	
C <sub>pd</sub> Power dissipation capacitance	No load	40	pF	

### **6 Parameter Measurement Information**

 $t_{pd}$  is the maximum between  $t_{PLH}$  and  $t_{PHL}$   $t_{t}$  is the maximum between  $t_{TLH}$  and  $t_{THL}$   $t_{dis}$ is the maximum between  $t_{PLZ}$  and  $t_{PHZ}$   $t_{en}$  is the maximum between  $t_{PZL}$  and  $t_{PZH}$ 

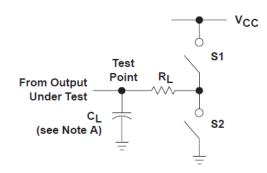


図 6-1. Load Circuit

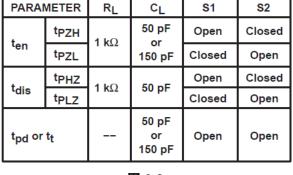


図 6-2.

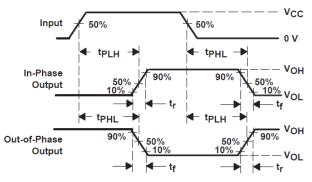


図 6-3. Voltage Waveforms
Propagation Delay and Output Transition Times

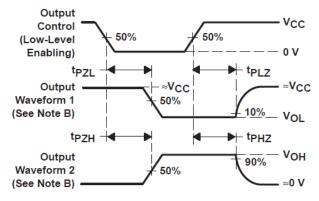


図 6-4. Voltage Waveforms
Enable and Disable Times for 3-State Outputs

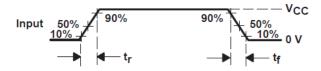


図 6-5. Voltage Wavefroms
Propagation Delay and Output Transition Times

- A. C<sub>L</sub> includes probe and test-fixture capacitance.
- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control.
- Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  1 MHz,  $Z_O$  = 50  $\Omega$ ,  $t_r$  = 6 ns,  $t_f$  = 6 ns.
- D. The outputs are measured one at a time with one input transition per measurement.

## 7 Detailed Description

## 7.1 Overview

These octal bus transceivers are designed for asynchronous two-way communication between data buses. These devices transmit data from the A bus to the B bus or from the B bus to the A bus, depending upon the level at the direction-control (DIR) input. The output-enable  $(\overline{OE})$  input can be used to disable the device so the buses are effectively isolated.

## 7.2 Functional Block Diagram

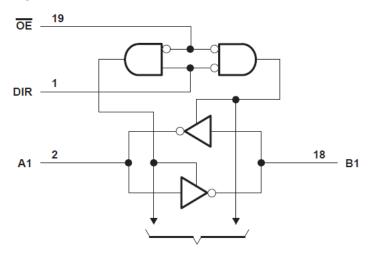


図 7-1. Functional Block Diagram

#### 7.3 Device Functional Modes

表 7-1. Function Table (each transceiver)

INPU	TS <sup>(1)</sup>	Operation
ŌĒ	DIR	Operation
L	L	B̄ data to A bus
L	Н	Ā data to B bus
Н	Х	Isolation

(1) H = High Voltage Level, L = Low Voltage Level, X = Don't Care



## 8 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each  $V_{CC}$  terminal should have a good bypass capacitor to prevent power disturbance. A 0.1- $\mu$ F capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1- $\mu$ F and 1- $\mu$ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

## 9 Layout

### 9.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or  $V_{\rm CC}$ , whichever makes more sense for the logic function or is more convenient.

## 10 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

### **10.1 Documentation Support**

#### 10.1.1 Related Documentation

## 10.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

### 10.3 サポート・リソース

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#### 10.4 Trademarks

TI E2E<sup>™</sup> is a trademark of Texas Instruments.

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### 10.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

#### 10.6 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

## 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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#### PACKAGING INFORMATION

Orderable part number	Status	Material type	Package   Pins	Package qty   Carrier	RoHS	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
						(4)	(5)		
5962-8780901RA	Active	Production	CDIP (J)   20	20   TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962-8780901RA SNJ54HC640J
SN54HC640J	Active	Production	CDIP (J)   20	20   TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	SN54HC640J
SN54HC640J.A	Active	Production	CDIP (J)   20	20   TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	SN54HC640J
SN74HC640DW	Obsolete	Production	SOIC (DW)   20	-	-	Call TI	Call TI	-40 to 85	HC640
SN74HC640DWR	Active	Production	SOIC (DW)   20	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HC640
SN74HC640DWR.A	Active	Production	SOIC (DW)   20	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HC640
SN74HC640N	Active	Production	PDIP (N)   20	20   TUBE	Yes	NIPDAU	N/A for Pkg Type	-40 to 85	SN74HC640N
SN74HC640N.A	Active	Production	PDIP (N)   20	20   TUBE	Yes	NIPDAU	N/A for Pkg Type	-40 to 85	SN74HC640N
SN74HC640NSR	Active	Production	SOP (NS)   20	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HC640
SN74HC640NSR.A	Active	Production	SOP (NS)   20	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HC640
SN74HC640PW	Obsolete	Production	TSSOP (PW)   20	-	-	Call TI	Call TI	-40 to 85	HC640
SN74HC640PWR	Active	Production	TSSOP (PW)   20	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HC640
SN74HC640PWR.A	Active	Production	TSSOP (PW)   20	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HC640
SNJ54HC640J	Active	Production	CDIP (J)   20	20   TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962-8780901RA SNJ54HC640J
SNJ54HC640J.A	Active	Production	CDIP (J)   20	20   TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962-8780901RA SNJ54HC640J

<sup>(1)</sup> **Status:** For more details on status, see our product life cycle.

<sup>(2)</sup> Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

<sup>(3)</sup> RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

<sup>(4)</sup> Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

## **PACKAGE OPTION ADDENDUM**

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(5) MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

#### OTHER QUALIFIED VERSIONS OF SN54HC640, SN74HC640:

Catalog: SN74HC640

Military: SN54HC640

NOTE: Qualified Version Definitions:

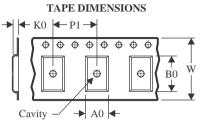
- Catalog TI's standard catalog product
- Military QML certified for Military and Defense Applications

# **PACKAGE MATERIALS INFORMATION**

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## TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

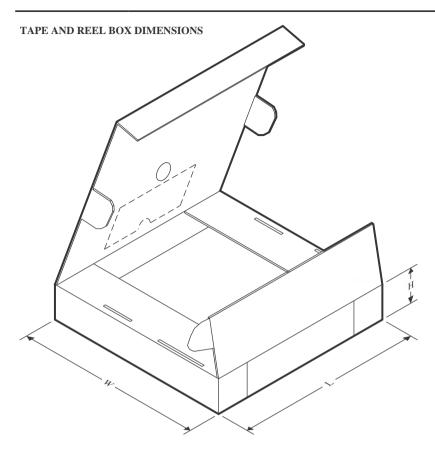


#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74HC640DWR	SOIC	DW	20	2000	330.0	24.4	10.9	13.3	2.7	12.0	24.0	Q1
SN74HC640DWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
SN74HC640NSR	SOP	NS	20	2000	330.0	24.4	8.4	13.0	2.5	12.0	24.0	Q1
SN74HC640PWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1



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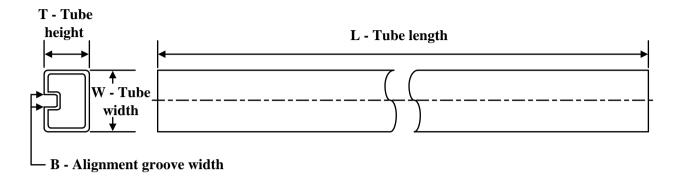
\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74HC640DWR	SOIC	DW	20	2000	356.0	356.0	45.0
SN74HC640DWR	SOIC	DW	20	2000	356.0	356.0	45.0
SN74HC640NSR	SOP	NS	20	2000	356.0	356.0	45.0
SN74HC640PWR	TSSOP	PW	20	2000	353.0	353.0	32.0

# **PACKAGE MATERIALS INFORMATION**

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## **TUBE**



### \*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN74HC640N	N	PDIP	20	20	506	13.97	11230	4.32
SN74HC640N.A	N	PDIP	20	20	506	13.97	11230	4.32

## **MECHANICAL DATA**

## NS (R-PDSO-G\*\*)

# 14-PINS SHOWN

## PLASTIC SMALL-OUTLINE PACKAGE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.



### 14 LEADS SHOWN



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. This package is hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
- E. Falls within MIL STD 1835 GDIP1-T14, GDIP1-T16, GDIP1-T18 and GDIP1-T20.

# N (R-PDIP-T\*\*)

## PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- The 20 pin end lead shoulder width is a vendor option, either half or full width.





SOIC



- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
- 5. Reference JEDEC registration MS-013.



SOIC



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOIC



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





SMALL OUTLINE PACKAGE



- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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